



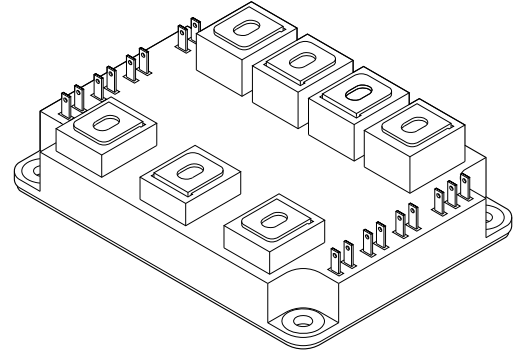
M.S.KENNEDY CORP.

# 600V/200A THREE PHASE BRIDGE PEM WITH BRAKE

# 4854

## FEATURES:

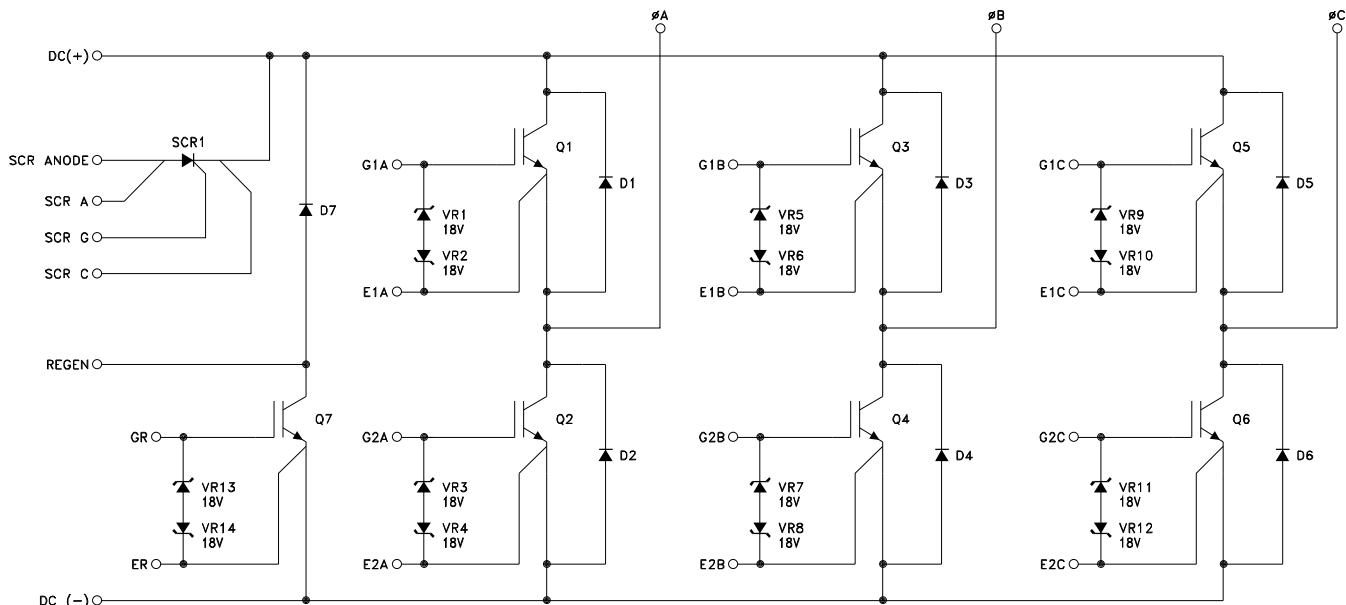
- Replaces MSK4851 with Lower Conduction Loss
- Full Three Phase Bridge Configuration with SCR/IGBT Brake
- 600V Rated Voltage
- 200A Continuous Output Current
- Internal Zener Clamps on Gates
- Encapsulation Provides Near Hermetic Performance
- HI-REL Screening Available (Modified 38534)
- Light Weight Domed AISiC Baseplate
- Robust Mechanical Design for Hi-Rel Applications
- Ultra-Low Inductance Internal Layout
- Withstands 96 Hours HAST and Thermal Cycling (-55°C to +125°C)



## DESCRIPTION:

The MSK4854 is one of a family of plastic encapsulated modules (PEM) developed specifically for use in military, aerospace and other severe environment applications. The Three Phase Bridge configuration along with the SCR/IGBT brake circuit and 600 volt/200 amp rating make it ideal for use in high current motor drive and inverter applications. The Aluminum Silicon Carbide (AlSiC) baseplate offers superior flatness and light weight; far better than the copper or copper alloys found in most high power plastic modules. The high thermal conductivity materials used to construct the MSK4854 allow high power outputs at elevated baseplate temperatures.

## EQUIVALENT SCHEMATIC



## TYPICAL APPLICATIONS

- Motor Drives
- Inverters

## ABSOLUTE MAXIMUM RATING <sup>⑧</sup>

V<sub>CE</sub> Collector to Emitter Voltage . . . . . 600V  
V<sub>GE</sub> Gate to Emitter Voltage . . . . . ± 20V  
I<sub>OUT</sub> Current (Continuous) . . . . . 200A  
I<sub>OUTP</sub> Current Pulsed (1mS) . . . . . 400A  
V<sub>CASE</sub> Case Isolation Voltage . . . . . 2500 V

T<sub>ST</sub> Storage Temperature Range <sup>⑨</sup> . . -55°C to +125°C  
T<sub>J</sub> Junction Temperature . . . . . 150°C  
T<sub>C</sub> Case Operating Temperature Range  
MSK4854H . . . . . -55°C to +125°C  
MSK4854 . . . . . -40°C to +85°C

## ELECTRICAL SPECIFICATIONS

Parameter <sup>⑥</sup>	Test Conditions	Group A Subgroup	MSK4854H			MSK4854			Units
			Min.	Typ.	Max.	Min.	Typ.	Max.	
Collector-Emitter Saturation Voltage	I <sub>C</sub> = 200A, V <sub>GE</sub> = 15V	1	-	1.80V	2.20V	-	1.80V	2.30V	V
		2	-	2.00V	2.40V	-	-	-	V
		3	-	1.60V	2.10V	-	-	-	V
Collector-Emitter Leakage Current	V <sub>CE</sub> = 600V, V <sub>GE</sub> = 0V	1	-	0.5	350	-	0.5	400	µA
		2	-	650	1700	-	-	-	µA
Gate Threshold Voltage	I <sub>C</sub> = 60mA, V <sub>CE</sub> = V <sub>GE</sub>	1	5.0	6.0	6.5	4.8	6.0	6.8	V
		2	4.0	5.0	6.5	-	-	-	V
		3	5.0	6.5	7.5	-	-	-	V
Gate Leakage Current	V <sub>CE</sub> = 0V, V <sub>GE</sub> = ± 15V	1	-	0.1	10	-	0.1	10	µA
		2	-	0.6	10	-	-	-	µA
		3	-	0.1	10	-	-	-	µA
Diode Forward Voltage	I <sub>C</sub> = 200A	1	-	1.70V	2.20V	-	1.70V	2.30V	V
		2	-	1.40V	2.20V	-	-	-	V
		3	-	1.80V	2.60V	-	-	-	V
SCR Reverse Leakage	V <sub>RRM</sub> = 600V	1	-	0.01	15	-	0.01	18	mA
		2	-	0.01	15	-	-	-	mA
		3	-	0.01	15	-	-	-	mA
SCR On Voltage	I <sub>F</sub> = 100A	1	-	1.0	1.35	-	1.0	1.4	V
		2	-	1.0	1.35	-	-	-	V
		3	-	1.0	1.35	-	-	-	V
SCR Holding Current		1	-	100	300	-	100	325	mA
		2	-	90	300	-	-	-	mA
		3	-	110	300	-	-	-	mA
Regen Diode Forward Voltage	I <sub>F</sub> = 50A	1	-	1.3	2.4	-	1.3	2.5	V
Total Gate Charge <sup>①</sup>	V = 300V, I <sub>C</sub> = 200A	4	-	1.0	1.5	-	1.0	1.6	µC
E(on) <sup>①</sup>	V = 300V, I <sub>C</sub> = 200A, R <sub>G</sub> = 5Ω, V <sub>GE</sub> = -7/+15V	4	-	6	-	-	6	-	mJ
	V = 300V, I <sub>C</sub> = 100A, R <sub>G</sub> = 5Ω, V <sub>GE</sub> = -7/+15V	4	-	3	6	-	3	7	mJ
E(off) <sup>①</sup>	V = 300V, I <sub>C</sub> = 200A, R <sub>G</sub> = 10Ω, V <sub>GE</sub> = -7/+15V	4	-	9	-	-	9	-	mJ
	V = 300V, I <sub>C</sub> = 100A, R <sub>G</sub> = 10Ω, V <sub>GE</sub> = -7/+15V	4	-	5	8	-	5	9	mJ
Diode Reverse Recovery Time <sup>①</sup>	I <sub>E</sub> = 200, di/dt = 2770A/µS	4	-	56	-	-	56	-	nS
	I <sub>E</sub> = 100, di/dt = 2770A/µS	4	-	47	-	-	47	-	nS
Diode Reverse Energy <sup>①</sup>	I <sub>E</sub> = 200, di/dt = 2770A/µS	4	-	0.5	-	-	0.5	-	mJ
	I <sub>E</sub> = 100, di/dt = 2770A/µS	4	-	0.4	2.4	-	0.4	-	mJ
Thermal Resistance <sup>①</sup>	IGBT @ T <sub>J</sub> = 125°C	-	-	0.21	0.26	-	0.21	0.26	°C/W
	DIODE @ T <sub>J</sub> = 125°C	-	-	0.17	0.21	-	0.17	0.21	°C/W

### NOTES:

- ① Guaranteed by design but not tested. Typical parameters are representative of actual device performance but are for reference only.
- ② Industrial grade devices shall be tested to subgroup 1 unless otherwise specified.
- ③ HI-REL grade devices ("H" suffix) shall be 100% tested to subgroups 1, 2 and sample tested to subgroup 3.
- ④ Subgroup 4 testing available upon request.
- ⑤ Subgroup 1, 4 T<sub>A</sub> = +25°C  
2 T<sub>A</sub> = +125°C  
3 T<sub>A</sub> = -55°C
- ⑥ All specifications apply to both the upper and lower sections of the half bridge.
- ⑦ V<sub>GE</sub> = 15V unless otherwise specified.
- ⑧ Continuous operation at or above absolute maximum ratings may adversely effect the device performance and/or life cycle.
- ⑨ Internal solder reflow temperature is 180°C, do not exceed.

***THERMAL CALCULATIONS***

Power dissipation and maximum allowable temperature rise involve many variables working together. Collector current, PWM duty cycle and switching frequency all factor into power dissipation. DC losses or "ON-TIME" losses are simply  $V_{CE(SAT)} \times \text{Collector Current} \times \text{PWM duty cycle}$ . For the MSK4854,  $V_{CE(SAT)} = 2.2V$  max., and at 200 amps and a PWM duty cycle of 30%, DC losses equal 132 watts. Switching losses, in milli-joules, vary proportionally with switching frequency. The MSK4854 typical switching losses at  $V_{CE} = 300V$  and  $I_{CE} = 200A$  are about 15mJ, which is simply the sum of the turn-on switching loss and the turn-off switching loss. Multiplying the switching frequency times the switching losses will result in a power dissipation number for switching. The MSK4854, at 15KHz, will exhibit switching power dissipation of 225 watts. The total losses are the sum of DC losses plus switching losses, or in this case, 357 watts total.  $357 \text{ watts} \times 0.26^\circ\text{C/W}$  thermal resistance equals 92.8 degrees of temperature rise between the case and the junction. Subtracting  $93^\circ\text{C}$  from the maximum junction temperature of  $150^\circ\text{C}$  equals  $57^\circ\text{C}$  maximum case temperature for this example.

$$V_{CE(SAT)} \times I_C \times \text{PWM duty cycle} = 2.2V \times 200 \text{ amps} \times 30\% = 132 \text{ watts DC losses}$$

$$\text{Turn-on switching loss} + \text{Turn-off switching loss} = \text{Total switching losses} = 6 + 9 = 15\text{mJ}$$

$$\text{Total switching loss} \times \text{PWM frequency} = \text{Total switching power dissipation} = 15\text{mJ} \times 15\text{KHz} = 225 \text{ watts}$$

$$\text{Total power dissipation} = \text{DC losses} + \text{switching losses} = 132 + 225 = 357 \text{ watts}$$

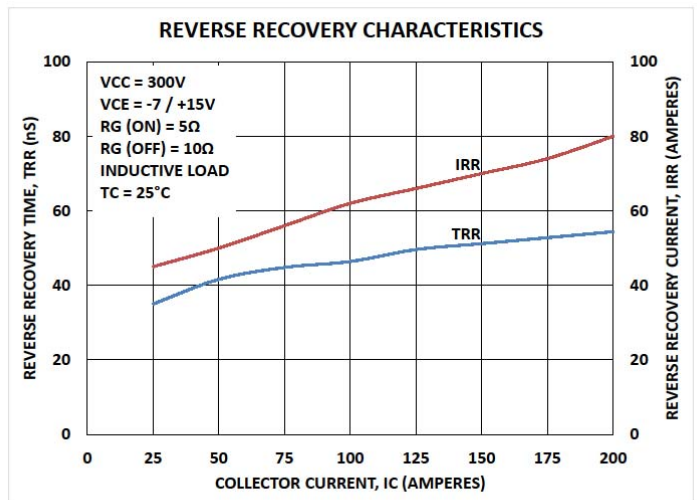
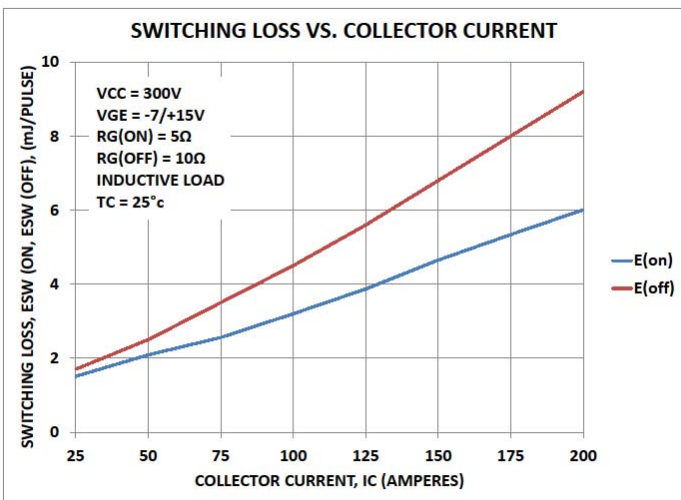
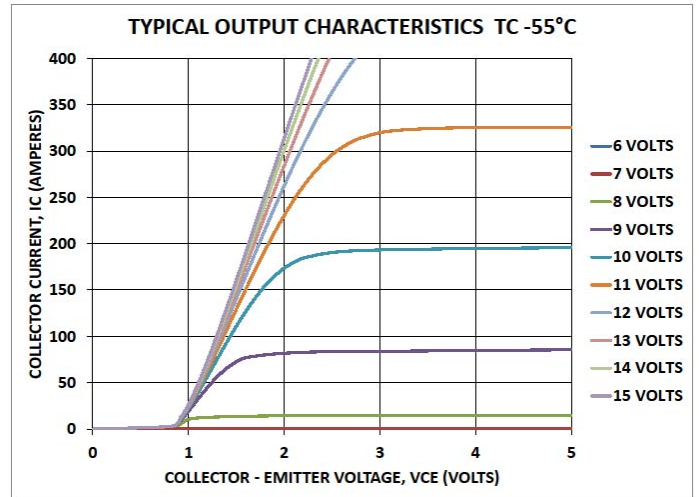
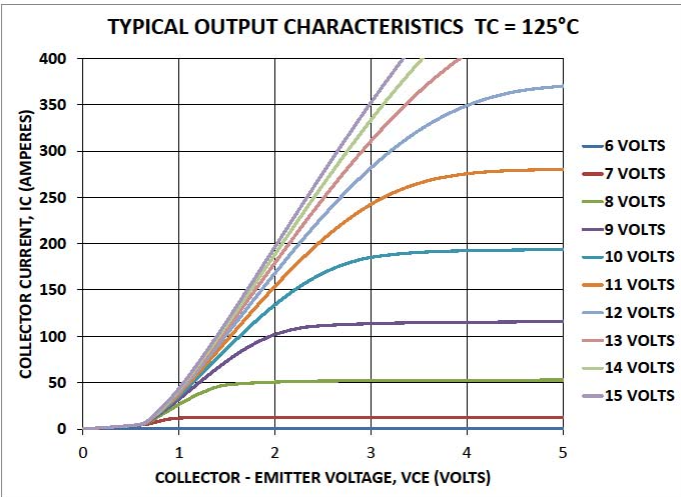
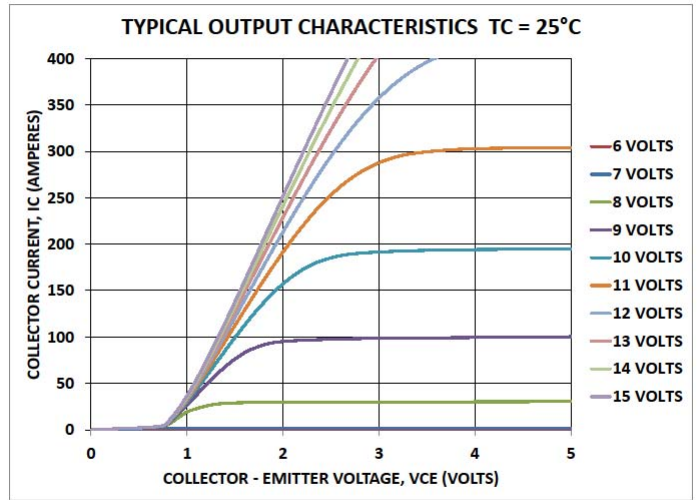
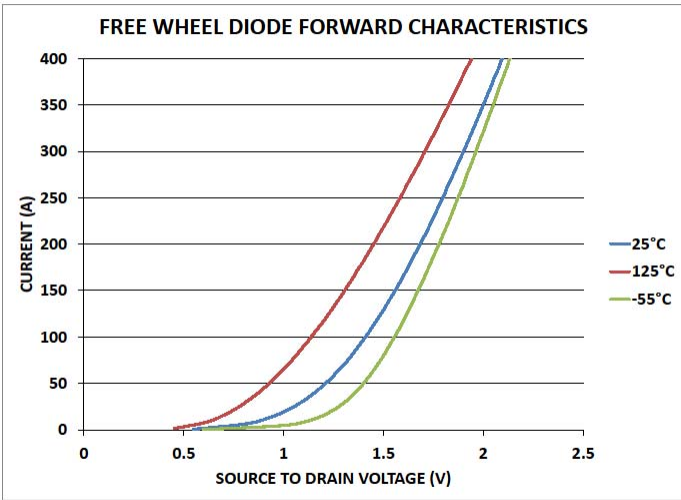
$$\text{Junction temperature rise above case} = \text{Total power dissipation} \times \text{thermal resistance}$$

$$357 \text{ watts} \times 0.26^\circ\text{C/W} = 92.8^\circ\text{C temperature rise above case}$$

$$\text{Maximum junction temperature} - \text{junction temperature rise} = \text{maximum baseplate temperature}$$

$$150^\circ\text{C} - 93^\circ\text{C} = 57^\circ\text{C}$$

# TYPICAL PERFORMANCE CURVES

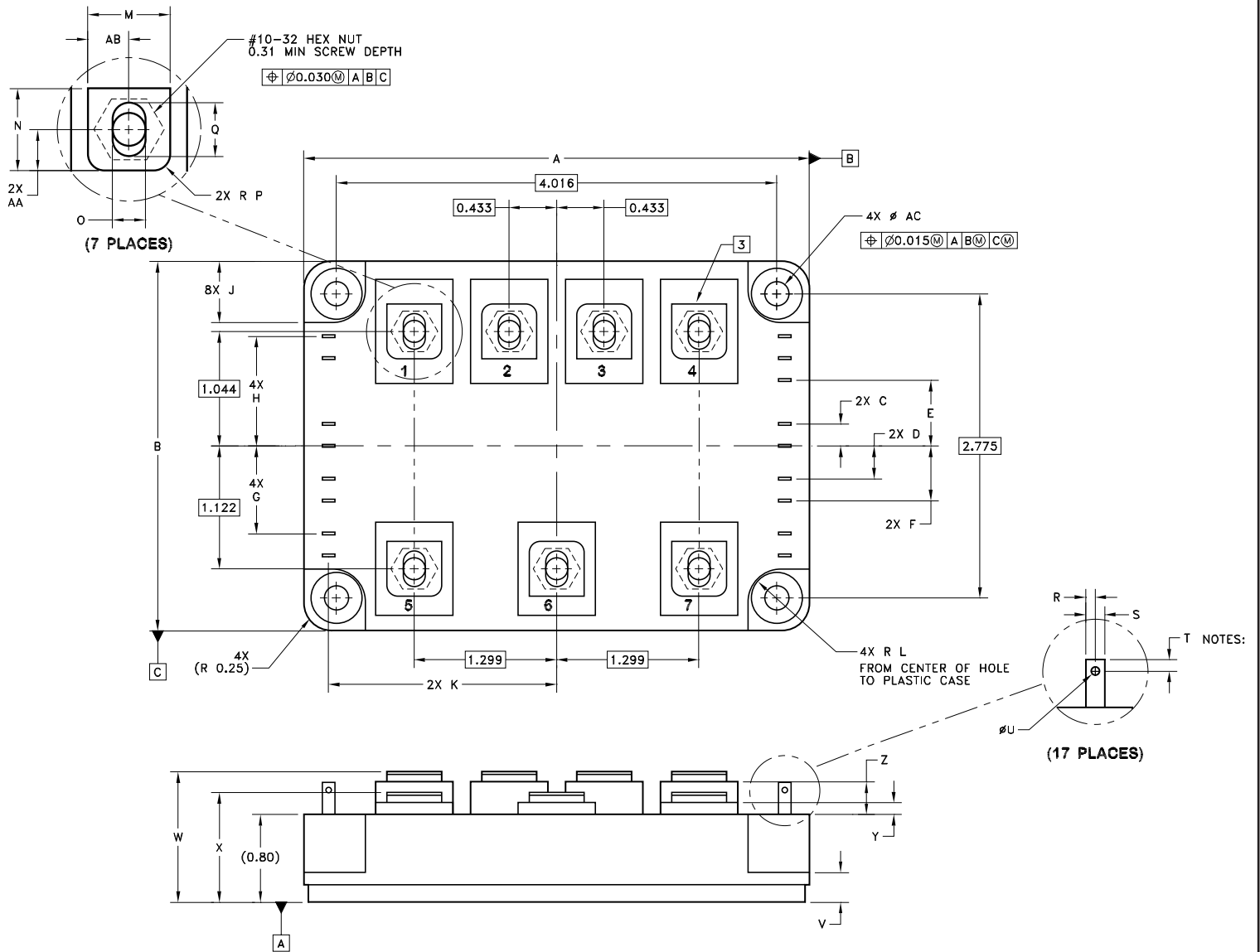


## SCREENING CHART

OPERATION	INDUSTRIAL	H SUFFIX
QUALIFICATION (MODIFIED)	NO	YES
ELEMENT EVALUATION	NO	YES
CLEAN ROOM PROCESSING	YES	YES
NON DESTRUCT BOND PULL SAMPLE	YES	YES
CERTIFIED OPERATORS	NO	YES
MIL LINE PROCESSING	YES	YES
MAX REWORK SPECIFIED	NO	YES
ENCAPSULANT	GEL COAT	GEL COAT
PRE-CAP VISUAL	YES - INDUSTRIAL	YES - CLASS H
TEMP CYCLE (-55°C TO +125°C)	NO	YES
BURN-IN	NO	YES - 160 HOURS
ELECTRICAL TESTING	YES - 25°C	YES - FULL TEMP
EXTERNAL VISUAL	YES - SAMPLE	YES
XRAY	NO	NO
PIN FINISH	NI	NI

NOTE: ADDITIONAL SCREENING IS AVAILABLE SUCH AS XRAY, CSAM, MECHANICAL SHOCK, ETC. CONTACT FACTORY FOR QUAL STATUS.

# MECHANICAL SPECIFICATIONS

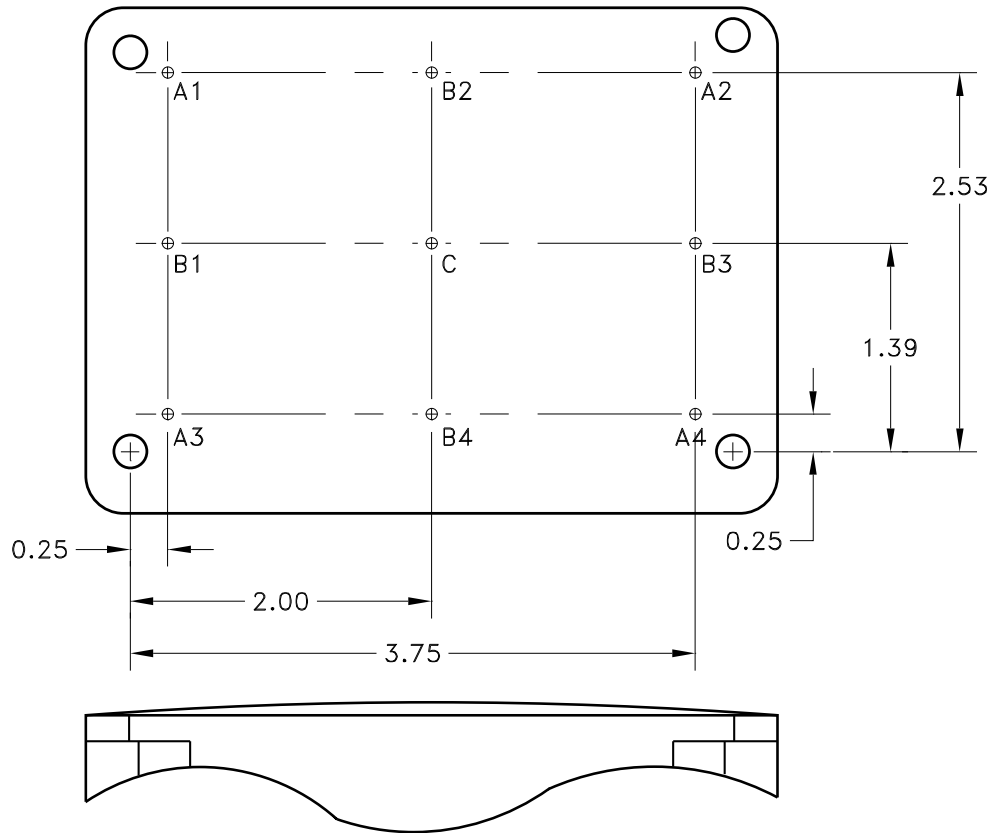


WEIGHT = 442 GRAMS TYPICAL

ALL DIMENSIONS ARE SPECIFIED IN INCHES

FOR CONVEX BASEPLATE PROFILE SEE SHEET 7

## MECHANICAL SPECIFICATIONS CONT'D



POWER MODULE SIDE VIEW (EXAGGERATED DOME)

NOTE:

1.(A1, A2, A3, B1, B2, B3 & B4) REFERENCED TO POINT C.

### CONVEX BASEPLATE PROFILE

REF	ZMIN	ZMAX
A1	0.000	0.010
A2	0.000	0.010
A3	0.000	0.010
A4	0.000	0.010
B1	0.000	0.010
B2	0.000	0.010
B3	0.000	0.010
B4	0.000	0.010

ALL DIMENSIONS ARE SPECIFIED IN INCHES

## ORDERING INFORMATION

MSK4854 H

SCREENING

BLANK = INDUSTRIAL; H = HI-REL (MODIFIED 38534)

GENERAL PART NUMBER

THE ABOVE EXAMPLE IS A HI-REL SCREENED MODULE.

## REVISION HISTORY

REV	STATUS	DATE	DESCRIPTION
E	Released	05/14	Update electrical specifications, mechanical outline, add performance curves and new form number.

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